



Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	20	V
Drain Current		$I_D(T_c=25^\circ\text{C})$	8	A
Gate-Source Voltage		V_{GS}	± 12	V
Avalanche Current		I_{AS}	12.5	A
Single Pulsed Avalanche Energy		E_{AS}	111	mJ
Power Dissipation		$P_D(T_c=25^\circ\text{C})$	2.8	W
Junction Temperature Range		T_j	150	
Storage Temperature Range		T_{stg}	-55 ~ 150	
Maximum Junction-to-Ambient	$t \leq 10\text{s}$	$R_{\theta JA}$	45	/W
	Steady-State	$R_{\theta JA}$	80	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DS}	$V_{GS}=0\text{V}$ $I_D=250\mu\text{A}$	20	25		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20\text{V}$ $V_{GS}=0\text{V}$			1.0	μA
		$V_{DS}=16\text{V}$ $T_J=150$			50	
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 12\text{V}$ $V_{DS}=0\text{V}$			± 0.1	μA
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}$ $I_D=8.0\text{A}$		8	10	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$ $I_D=8.0\text{A}$		9.5	11	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}$ $I_D=8.0\text{A}$		14	16	$\text{m}\Omega$ th 1.6686 TD

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Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	$Q_{g(4.5V)}$	$V_{DS}=10V$ $V_{GS}=4.5V$ $I_D=12.0A$		17.9		
Gate-Source Charge	Q_{gs}			1.5		nC

/ Electrical Characteristic Curve

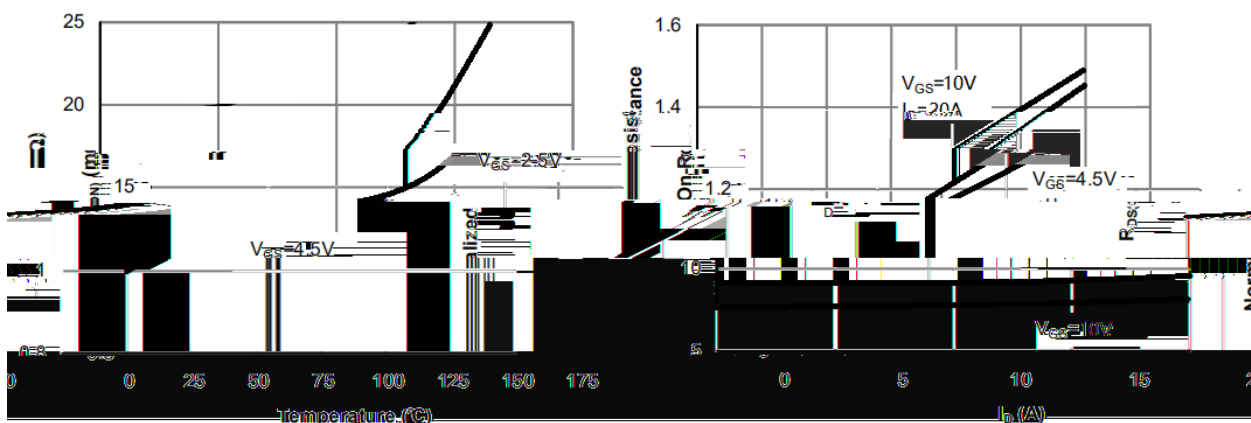
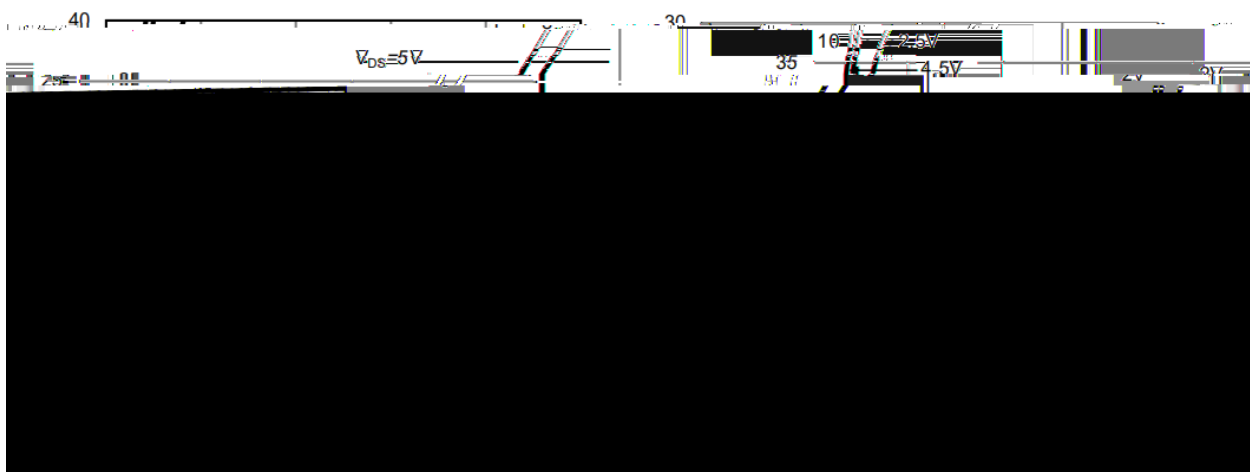


Figure 1: On-Resistance vs. Drain Current and Temperature

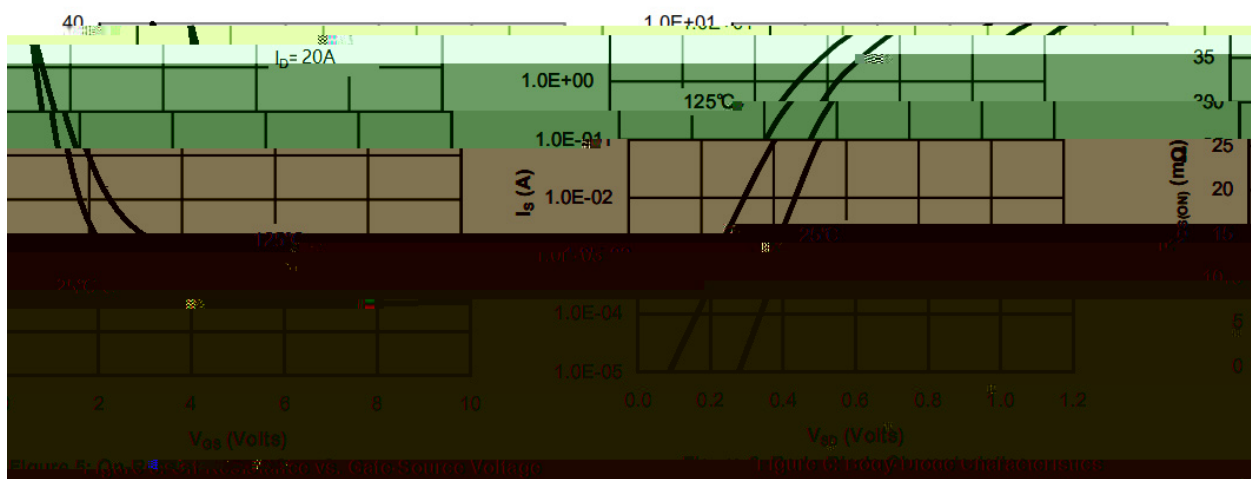
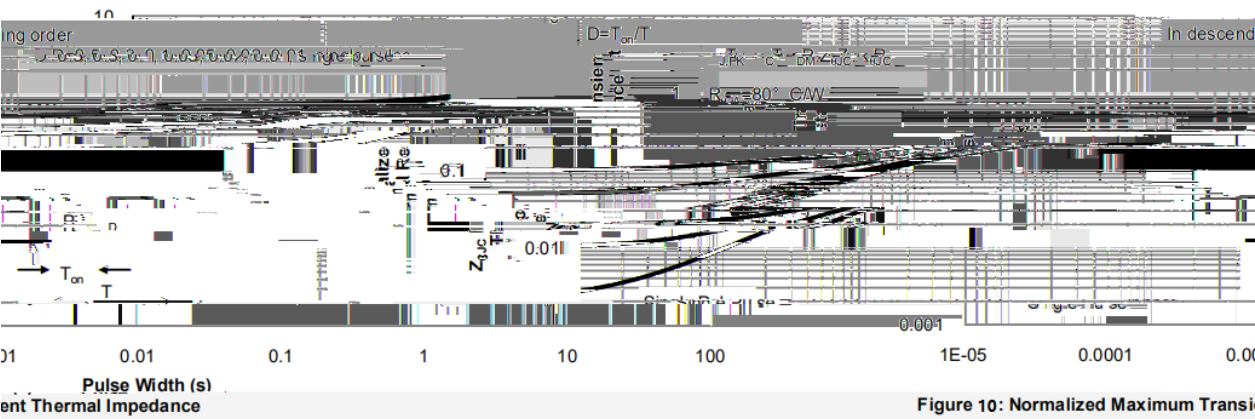
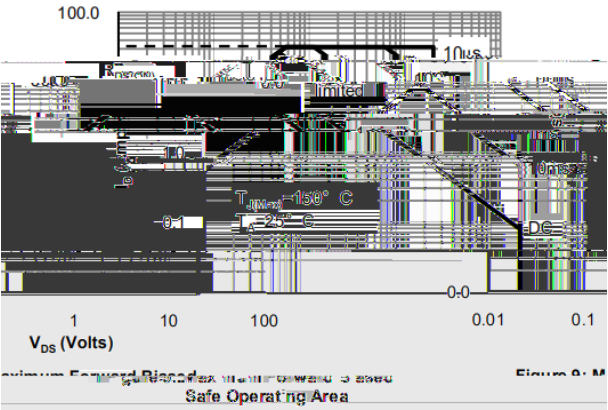
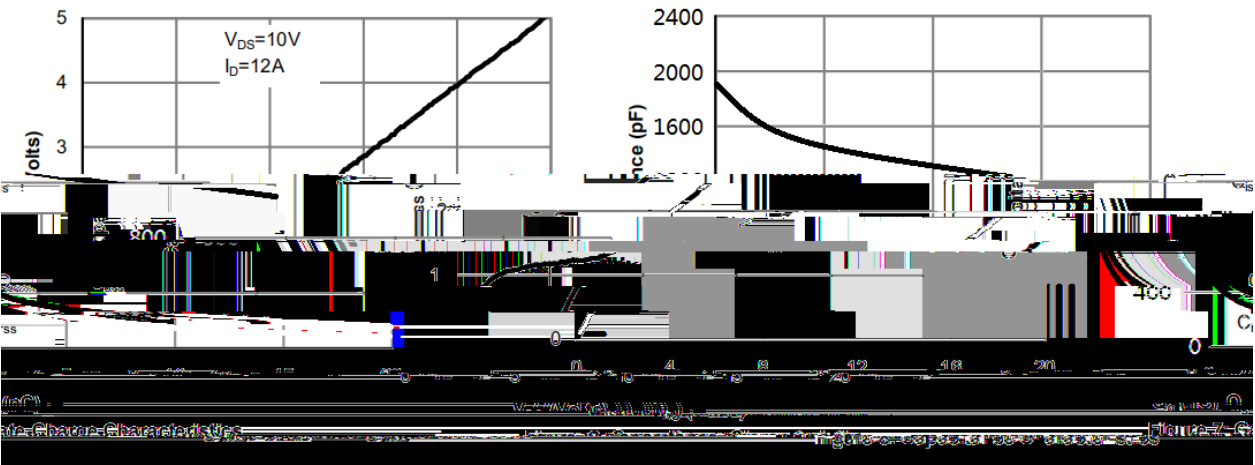


Figure 3: On-Resistance vs. Drain Current and Temperature

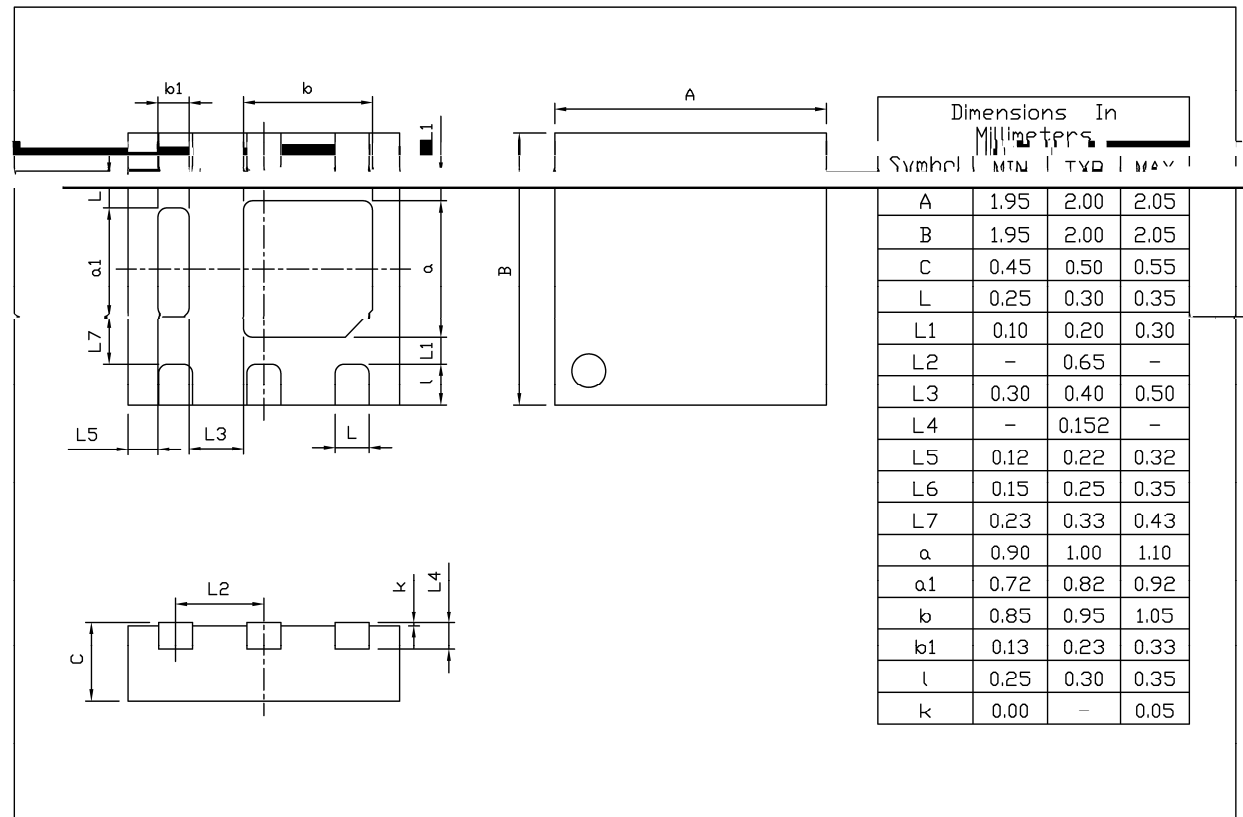
/ Electrical Characteristic Curve



/ Package Dimensions

DFN2 X2B-6L-0.5

Unit:mm



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